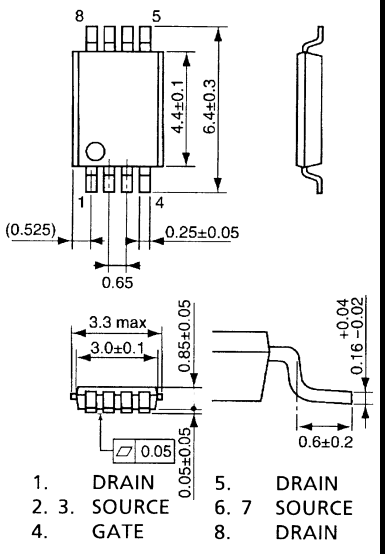
TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOS II)

TPCS8102

Lithium-Ion Battery Applications
Portable Equipment Applications
Notebook PC Applications

- Small footprint due to a small and slim package
- Low drain-source ON resistance: $R_{DS\ (ON)}$ = 16 mΩ (typ.)
- High forward transfer admittance: $|Y_{fs}|$ = 17 S (typ.)
- Low leakage current: I_{DSS} = −10 μA (max.) (V_{DS} = −20 V)
- Enhancement mode: V_{th} = −0.5~−1.2 V (V_{DS} = −10 V, I_D = −200 μA)

Unit: mm



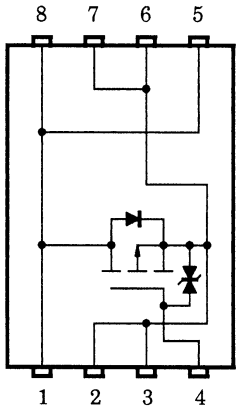
JEDEC	—
JEITA	—
TOSHIBA	2-3R1B

Weight: 0.035 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	−20	V
Drain-gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	−20	V
Gate-source voltage		V_{GSS}	±12	V
Drain current	DC (Note 1)	I_D	−6	A
	Pulse (Note 1)	I_{DP}	−24	
Drain power dissipation (t = 10 s) (Note 2a)		P_D	1.5	W
Drain power dissipation (t = 10 s) (Note 2b)		P_D	0.6	W
Single-pulse avalanche energy (Note 3)		E_{AS}	46.8	mJ
Avalanche current		I_{AR}	−6	A
Repetitive avalanche energy (Note 2a, Note 4)		E_{AR}	0.15	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

Circuit Configuration



Note: For Notes 1 to 5, see the next page.

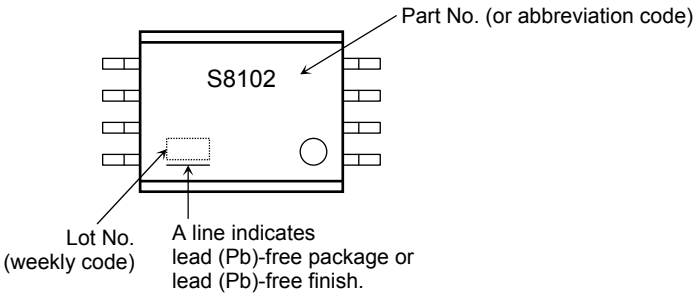
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	$R_{th\ (ch\text{-}a)}$	83.3	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	$R_{th\ (ch\text{-}a)}$	208	°C/W

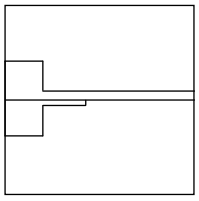
Marking (Note 5)



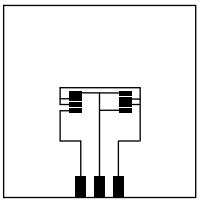
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:

a) Device mounted on a glass-epoxy board (a)



b) Device mounted on a glass-epoxy board (b)

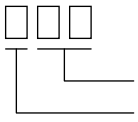


Note 3: V_{DD} = −16 V, T_{ch} = 25°C (initial), L = 1.0 mH, R_G = 25 Ω, I_{AR} = −6.0 A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: ○ on the lower right of the marking indicates Pin 1.

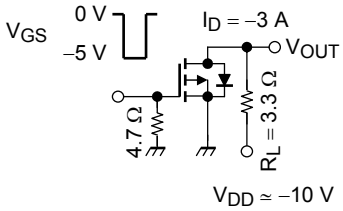
* Weekly code: (Three digits)



Week of manufacture
(“01” for the first week of the year, continuing up to “52” or “53”)

Year of manufacture
(the last digit of the calendar year)

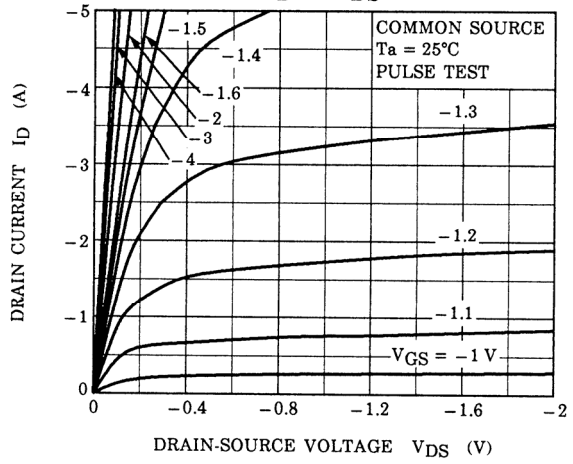
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min.	Typ.	Max.	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±10 V, V_{DS} = 0 V	—	—	±10	μA
Drain cut-off current		I_{DSS}	V_{DS} = −20 V, V_{GS} = 0 V	—	—	−10	μA
Drain-source breakdown voltage		$V_{(BR)\ DSS}$	I_D = −10 mA, V_{GS} = 0 V	−20	—	—	V
		$V_{(BR)\ DSX}$	I_D = −10 mA, V_{GS} = 12 V	−8	—	—	
Gate threshold voltage		V_{th}	V_{DS} = −10 V, I_D = −200 μA	−0.5	—	−1.2	V
Drain-source ON resistance		$R_{DS\ (ON)}$	V_{GS} = −2.0 V, I_D = −3 A	—	30	60	mΩ
		$R_{DS\ (ON)}$	V_{GS} = −2.5 V, I_D = −3 A	—	23	38	
		$R_{DS\ (ON)}$	V_{GS} = −4 V, I_D = −3 A	—	16	20	
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = −10 V, I_D = −3 A	8.5	17	—	S
Input capacitance		C_{iss}	V_{DS} = −10 V, V_{GS} = 0 V, f = 1 MHz	—	2740	—	pF
Reverse transfer capacitance		C_{rss}		—	780	—	pF
Output capacitance		C_{oss}		—	1030	—	pF
Switching time	Rise time	t_r		—	7.6	—	ns
	Turn-on time	t_{on}		—	16	—	
	Fall time	t_f		—	110	—	
	Turn-off time	t_{off}	Duty ≦ 1%, t_w = 10 μs	—	230	—	
Total gate charge (gate-source plus gate-drain)		Q_g	V_{DD} ≈ −16 V, V_{GS} = −5 V, I_D = −6 A	—	37	—	nC
Gate-source charge		Q_{gs}		—	27	—	nC
Gate-drain (“miller”) charge		Q_{gd}		—	10	—	nC

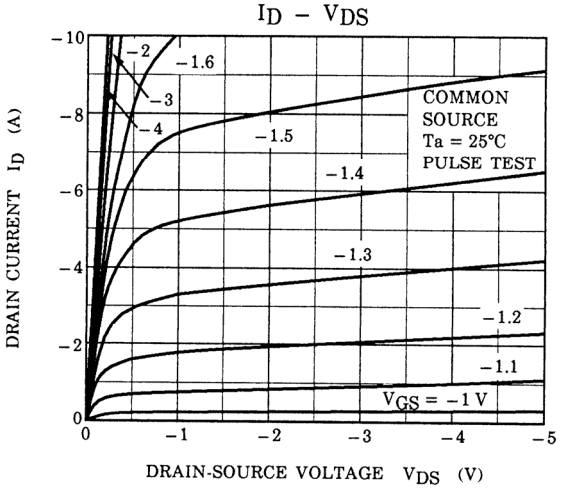
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	−24	A
Forward voltage (diode)		V_{DSF}	I_{DR} = −6 A, V_{GS} = 0 V	—	—	1.2	V

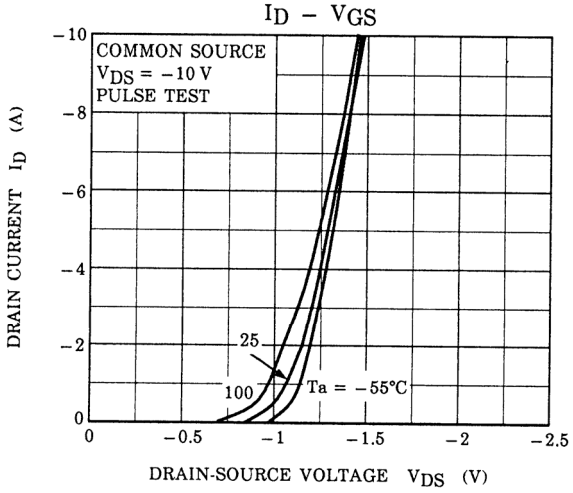
$I_D - V_{DS}$



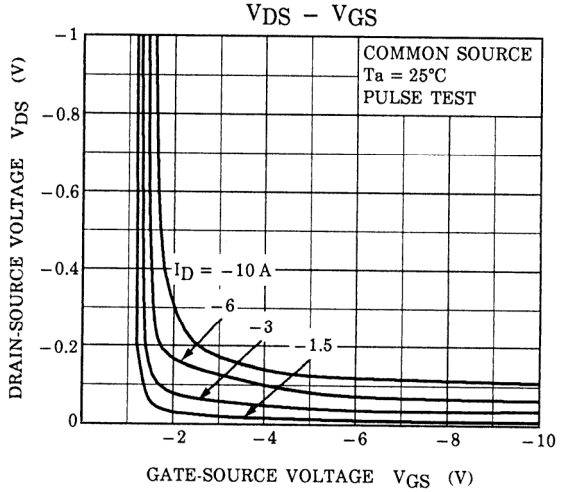
$I_D - V_{DS}$



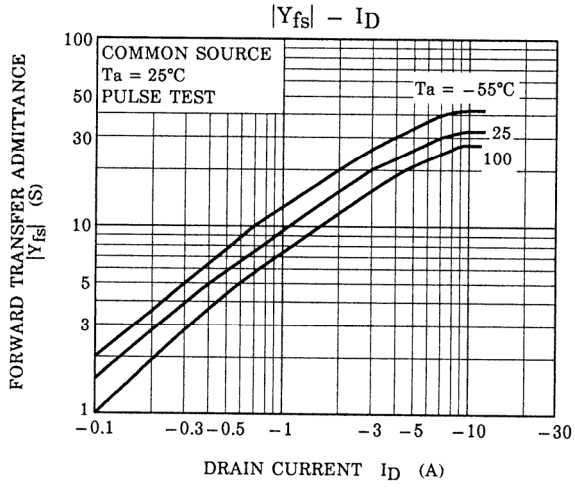
$I_D - V_{GS}$



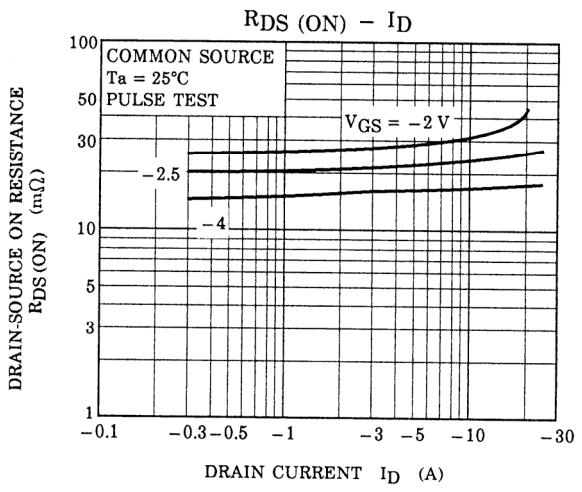
$V_{DS} - V_{GS}$



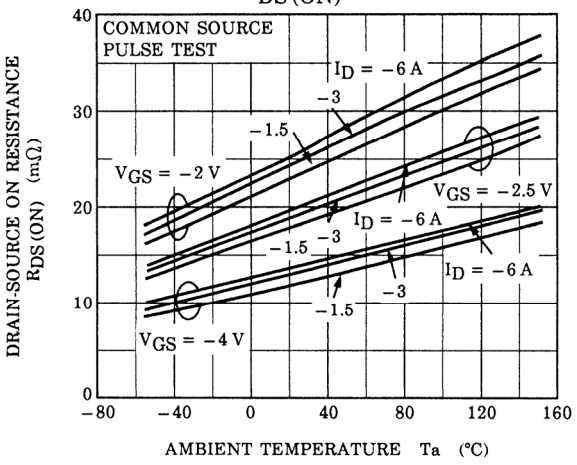
$|Y_{fs}| - I_D$



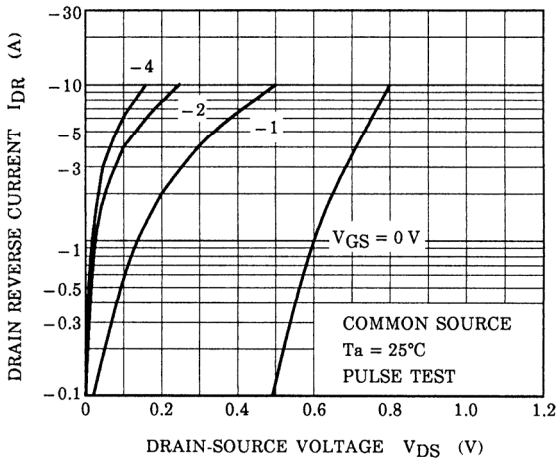
$R_{DS\ (ON)} - I_D$



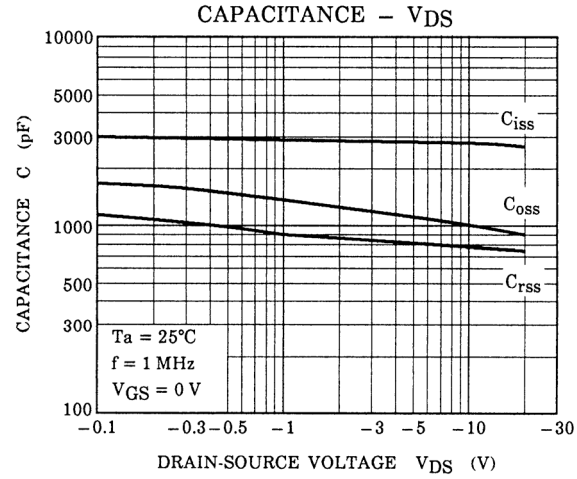
$R_{DS\,(ON)}$ – Ta



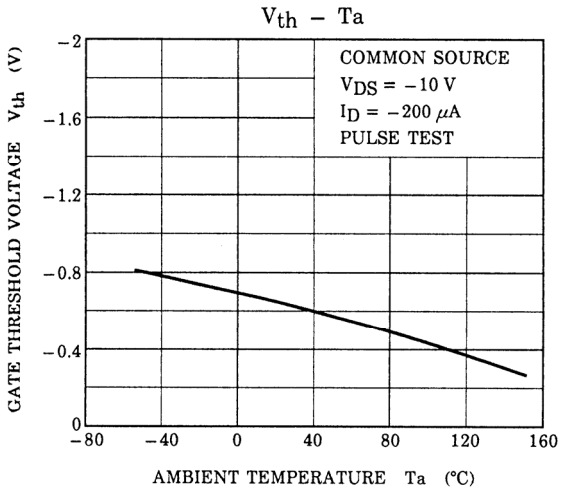
I_{DR} – V_{DS}



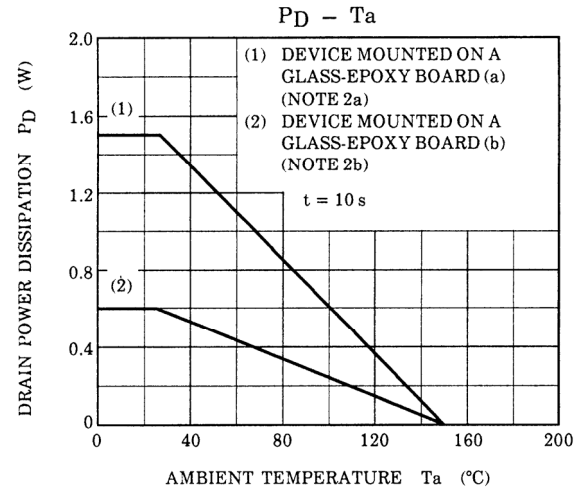
CAPACITANCE – V_{DS}



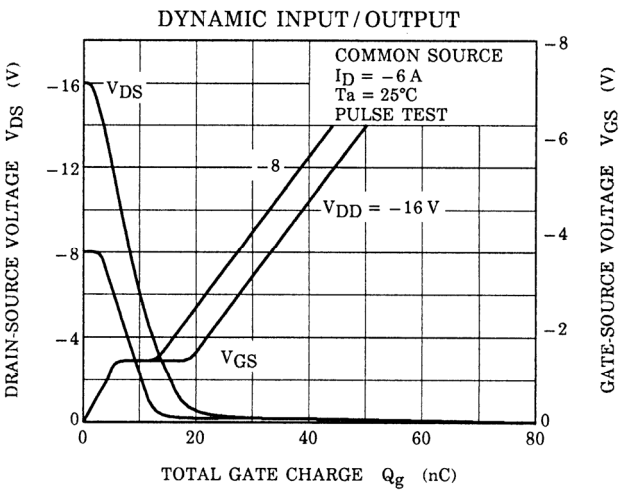
V_{th} – Ta



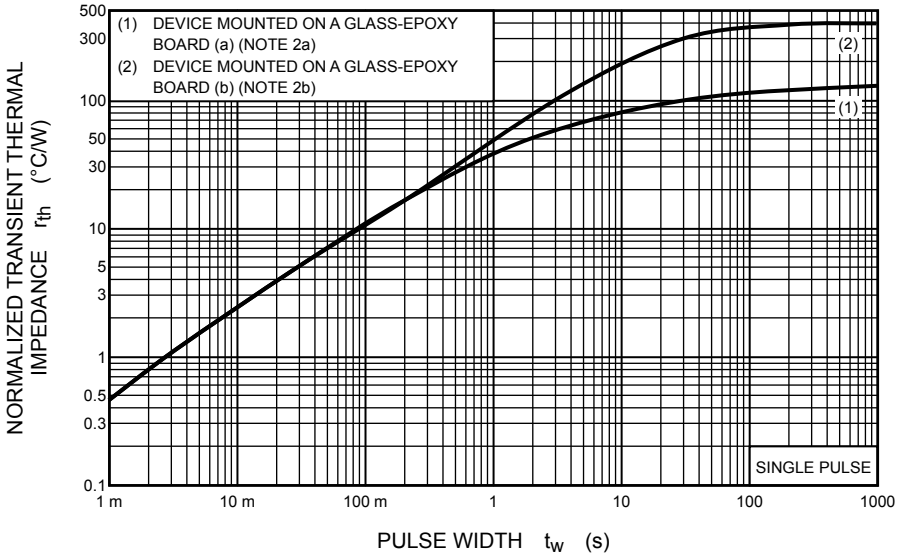
P_D – Ta

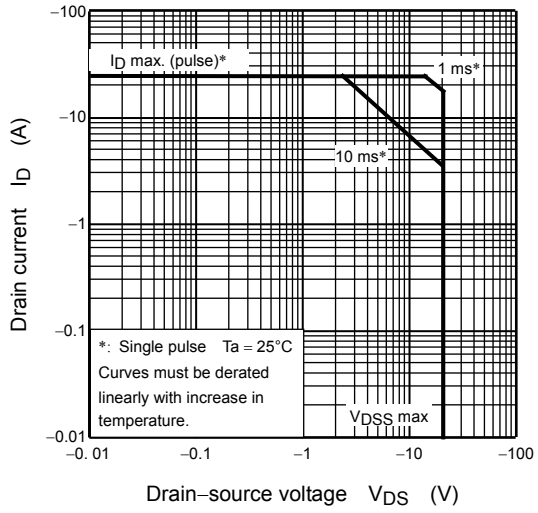


DYNAMIC INPUT / OUTPUT

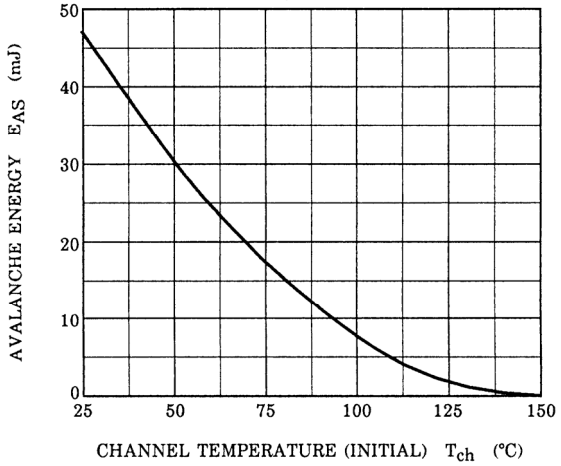


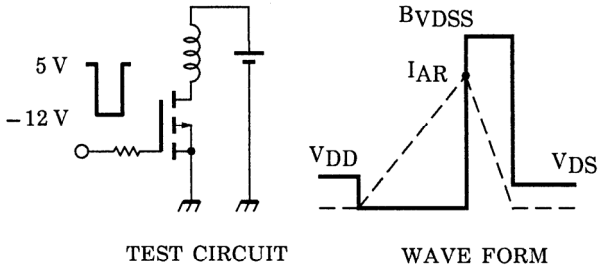
$r_{th} - t_w$





$E_{AS} - T_{ch}$





T_{ch} = 25°C (Initial)
Peak I_{AR} = −6 A, R_G = 25 Ω $E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}}\right)$
V_{DD} = −16 V, L = 1.0 mH

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20070701-EN

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